



4N65-Q

Power MOSFET

4A, 650V N-CHANNEL POWER MOSFET

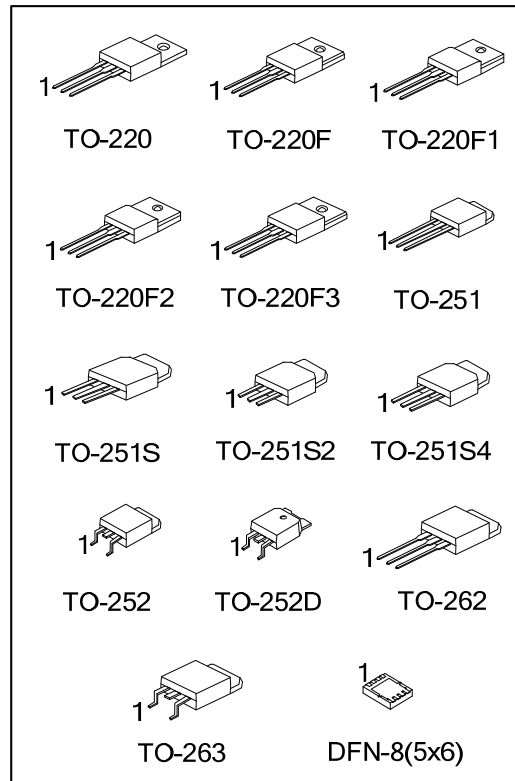
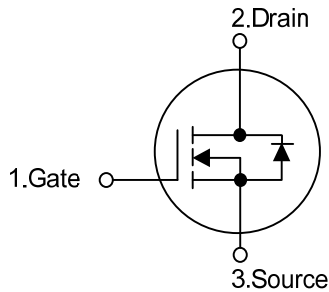
DESCRIPTION

The UTC **4N65-Q** is a high voltage power MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristic. This power MOSFET is usually used in high speed switching applications including power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 3.1\Omega$ @ $V_{GS} = 10V, I_D = 2.2A$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



ORDERING INFORMATION

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
4N65L-TA3-T	4N65G-TA3-T	TO-220	G	D	S	-	-	-	-	-	Tube
4N65L-TF1-T	4N65G-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	Tube
4N65L-TF2-T	4N65G-TF2-T	TO-220F2	G	D	S	-	-	-	-	-	Tube
4N65L-TF3T-T	4N65G-TF3T-T	TO-220F3	G	D	S	-	-	-	-	-	Tube
4N65L-TF3-T	4N65G-TF3-T	TO-220F	G	D	S	-	-	-	-	-	Tube
4N65L-TM3-T	4N65G-TM3-T	TO-251	G	D	S	-	-	-	-	-	Tube
4N65L-TMS-T	4N65G-TMS-T	TO-251S	G	D	S	-	-	-	-	-	Tube
4N65L-TMS2-T	4N65G-TMS2-T	TO-251S2	G	D	S	-	-	-	-	-	Tube
4N65L-TMS4-T	4N65G-TMS4-T	TO-251S4	G	D	S	-	-	-	-	-	Tube
4N65L-TN3-R	4N65G-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
4N65L-TND-R	4N65G-TND-R	TO-252D	G	D	S	-	-	-	-	-	Tape Reel
4N65L-T2Q-T	4N65G-T2Q-T	TO-262	G	D	S	-	-	-	-	-	Tube
4N65L-TQ2-R	4N65G-TQ2-R	TO-263	G	D	S	-	-	-	-	-	Tape Reel
4N65L-TQ2-T	4N65G-TQ2-T	TO-263	G	D	S	-	-	-	-	-	Tube
-	4N65G-K08-5060-R	DFN-8(5×6)	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>4N65L-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2 TF3: TO-220F, TF3T: TO-220F3, TM3: TO-251, TMS: TO-251S, TMS2: TO-251S2, TN3: TO-252, TMS4: TO-251S4, TND: TO-252D, T2Q: TO-262, TQ2: TO-263, K08-5060: DFN-8(5×6)</p> <p>(3) L: Lead Free, G: Halogen Free and Lead Free</p>
---	---

MARKING

PACKAGE	MARKING
TO-220 TO-220F TO-220F1 TO-220F2 TO-220F3 TO-251 TO-251S TO-251S2 TO-251S4 TO-252 TO-252D TO-262 TO-263	<p>UTC 4N65</p> <p>Lot Code ← → Data Code</p> <p>1</p> <p>L: Lead Free G: Halogen Free</p>
DFN-8(5×6)	<p>UTC 4N65</p> <p>Lot Code ← → Date Code</p>

■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT	
Drain-Source Voltage	V_{DSS}	650	V	
Gate-Source Voltage	V_{GSS}	± 30	V	
Avalanche Current (Note2)	I_{AR}	4.4	A	
Drain Current	Continuous	I_D	4.0	A
	Pulsed (Note2)	I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note3)	E_{AS}	60	mJ
	Repetitive (Note2)	E_{AR}	10.6	mJ
Peak Diode Recovery dv/dt (Note4)	dv/dt	4.5	V/ns	
Power Dissipation	TO-220/TO-262/TO-263	P_D	106	W
	TO-220F/TO-220F1		36	W
	TO-220F3			
	TO-220F2		38	W
	TO-251/TO-251S		50	W
	TO-251S2/TO-251S4			
TO-252/TO-252D				
DFN-8(5x6)	30	W		
Junction Temperature	T_J	+150	$^\circ\text{C}$	
Operating Temperature	T_{OPR}	-55 ~ +150	$^\circ\text{C}$	
Storage Temperature	T_{STG}	-55 ~ +150	$^\circ\text{C}$	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $L = 30\text{mH}$, $I_{AS} = 2.1\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 4.4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER	PACKAGE	SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-262/TO-263	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1			
	TO-220F2/TO-220F3			
	TO-251/ TO-251S		83	$^\circ\text{C}/\text{W}$
TO-251S2/TO-251S4				
TO-252/TO-252D				
	DFN-8(5x6)		75 (Note)	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220/TO-262/TO-263	θ_{JC}	1.18	$^\circ\text{C}/\text{W}$
	TO-220F/TO-220F1		3.47	$^\circ\text{C}/\text{W}$
	TP-220F3			
	TO-220F2		3.28	$^\circ\text{C}/\text{W}$
	TO-251/ TO-251S		2.5	$^\circ\text{C}/\text{W}$
	TO-251S2/TO-251S4			
	TO-252/TO-252D			
	DFN-8(5x6)		4.17 (Note)	$^\circ\text{C}/\text{W}$

Note: The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

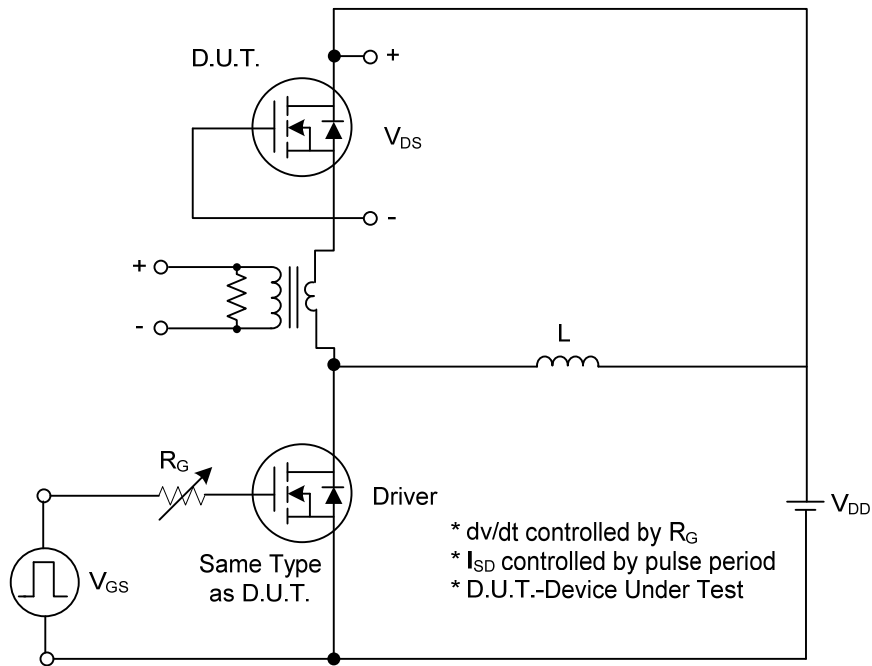
■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _D = 250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30 V, V _{DS} = 0 V		100	nA
	Reverse		V _{GS} = -30 V, V _{DS} = 0 V		-100	nA
Breakdown Voltage Temperature Coefficient	ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.6		V/°C
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 2.2A		2.9	3.1	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} = 25 V, V _{GS} = 0V, f = 1MHz		470	530	pF
Output Capacitance	C _{OSS}			50	70	pF
Reverse Transfer Capacitance	C _{RSS}			10	13	pF
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{D(ON)}	V _{DS} = 325V, I _D = 4.0A, R _G = 25Ω (Note 1, 2)		38	75	ns
Turn-On Rise Time	t _R			45	85	ns
Turn-Off Delay Time	t _{D(OFF)}			90	130	ns
Turn-Off Fall Time	t _F			35	80	ns
Total Gate Charge	Q _G	V _{DS} = 520V, I _D = 4.0A, V _{GS} = 10V (Note 1, 2)		55	75	nC
Gate-Source Charge	Q _{GS}			15	21	nC
Gate-Drain Charge	Q _{GD}			18	24	nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} = 0 V, I _S = 4.4A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I _S				4.4	A
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}				17.6	A
Reverse Recovery Time	t _{rr}	V _{GS} = 0V, I _S = 4.4A, dI _F /dt = 100 A/μs (Note 1)		250		ns
Reverse Recovery Charge	Q _{RR}			1.5		μC

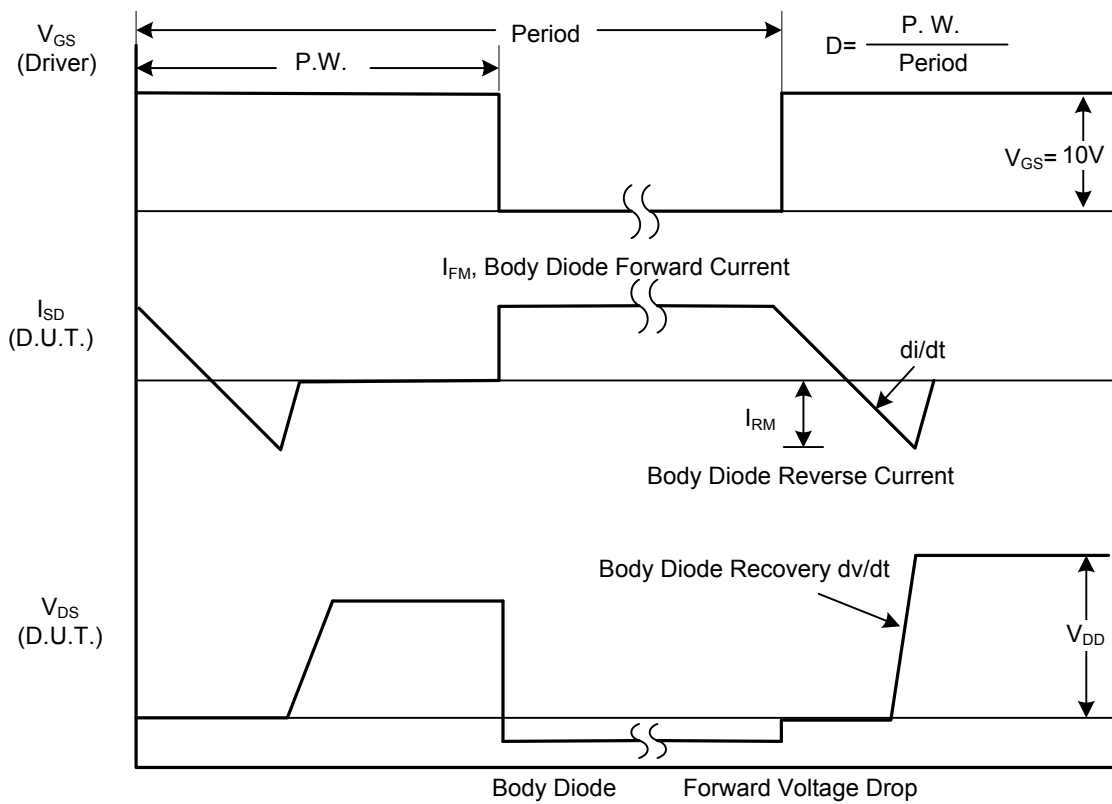
Note: 1. Pulse Test: Pulse width≤300μs, Duty cycle≤2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

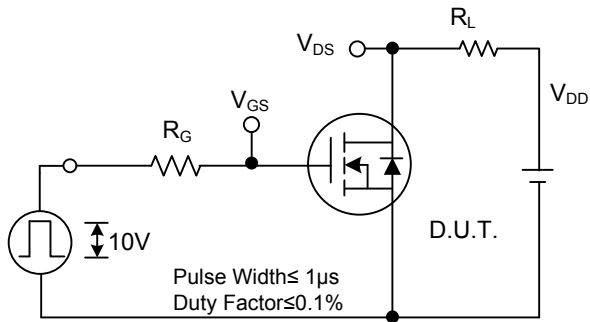


Peak Diode Recovery dv/dt Test Circuit

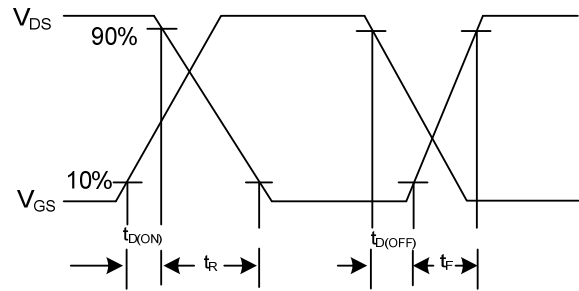


Peak Diode Recovery dv/dt Waveforms

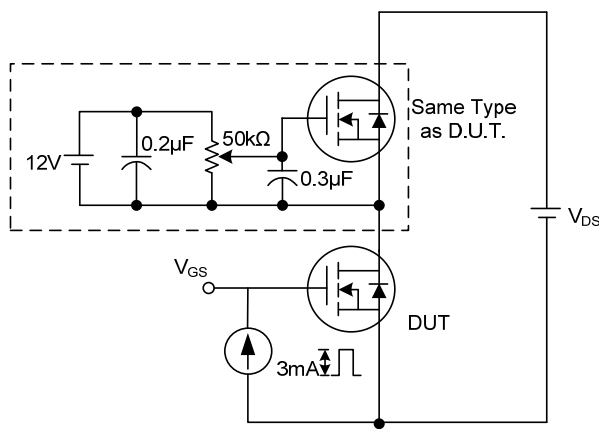
TEST CIRCUITS AND WAVEFORMS (Cont.)



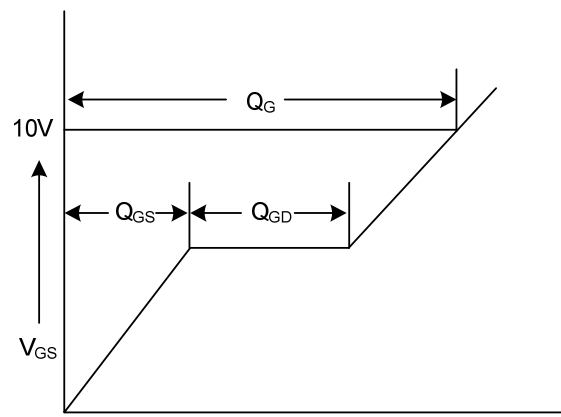
Switching Test Circuit



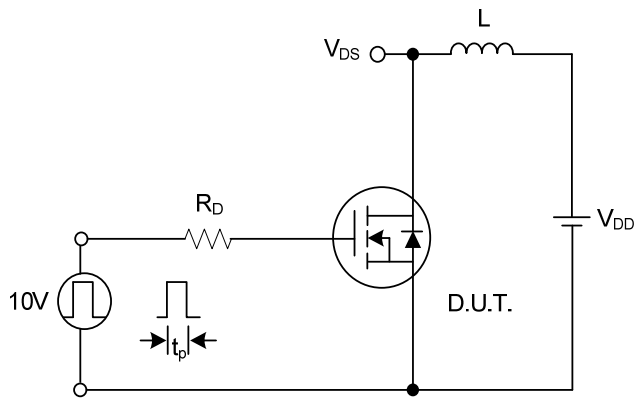
Switching Waveforms



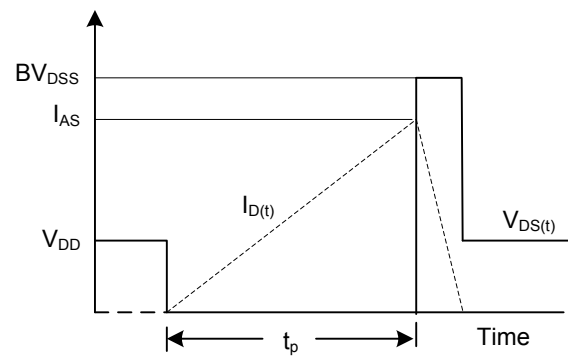
Gate Charge Test Circuit



Gate Charge Waveform

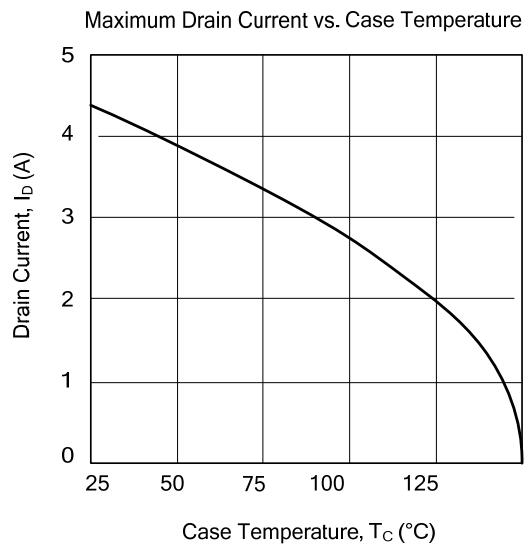
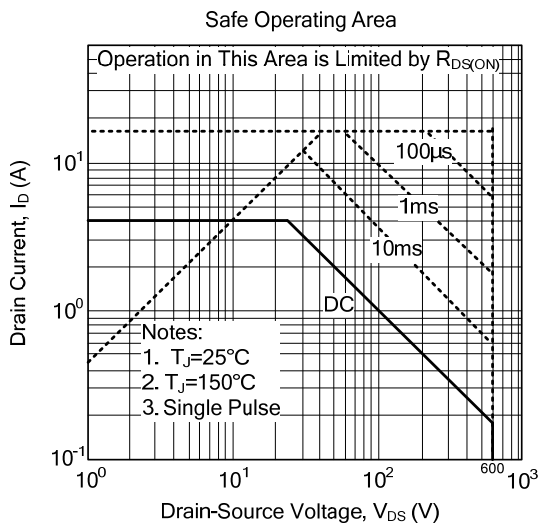
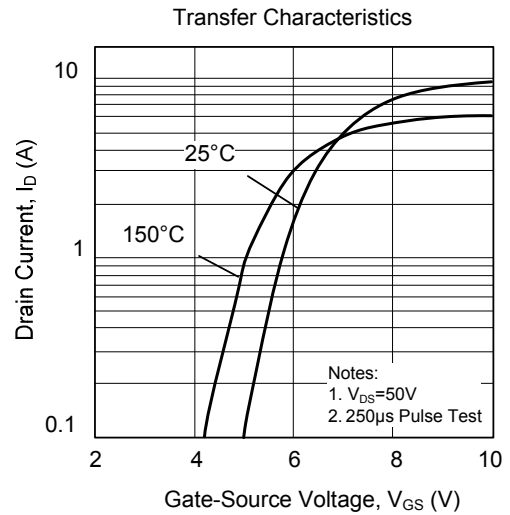
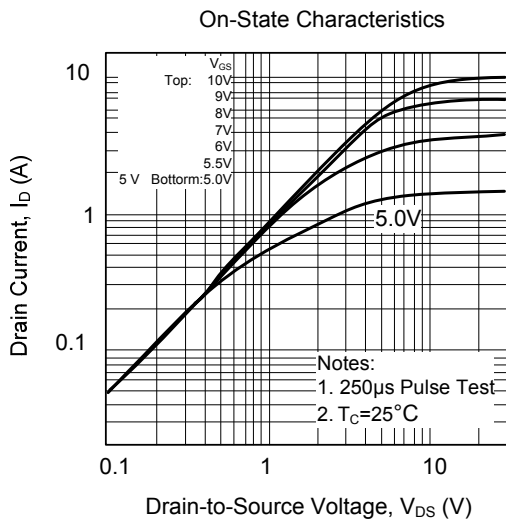
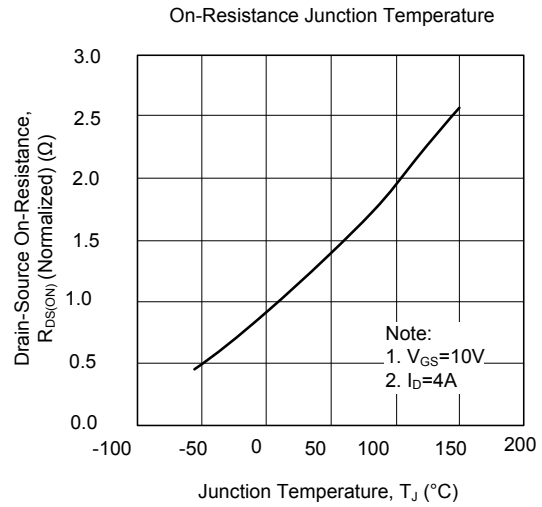
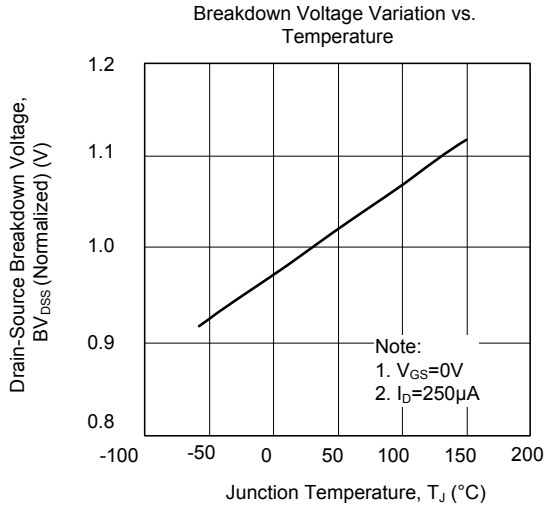


Unclamped Inductive Switching Test Circuit



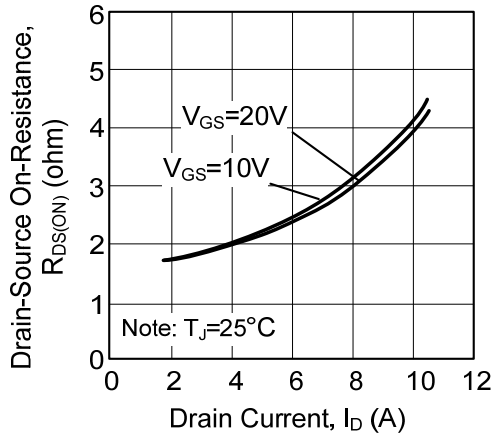
Unclamped Inductive Switching Waveforms

TYPICAL CHARACTERISTICS

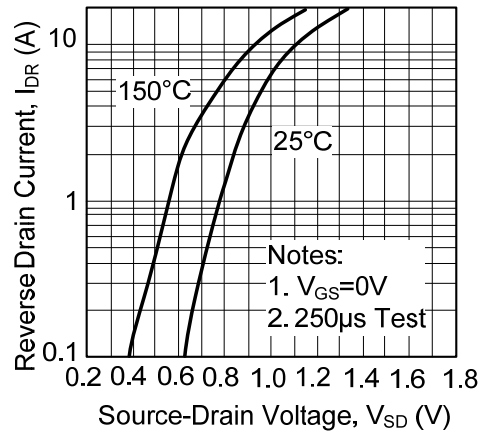


■ TYPICAL CHARACTERISTICS(Cont.)

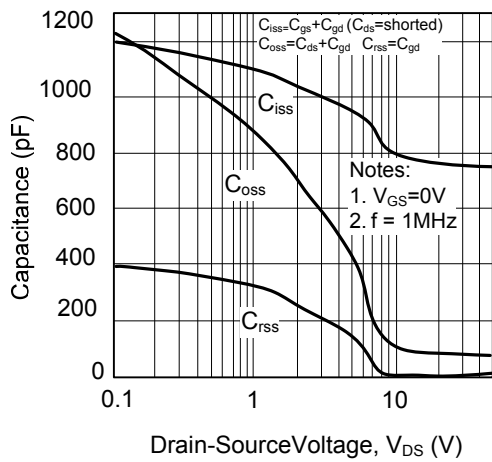
On-Resistance Variation vs. Drain Current and Gate Voltage



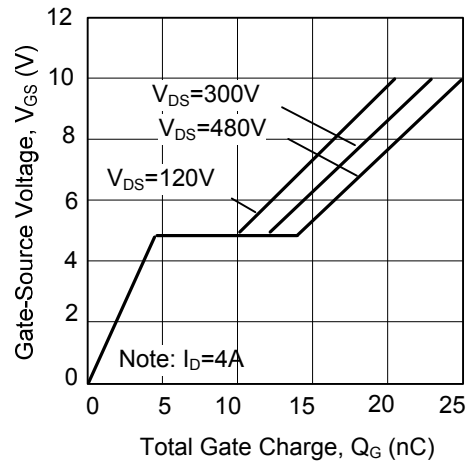
On State Current vs. Allowable Case Temperature



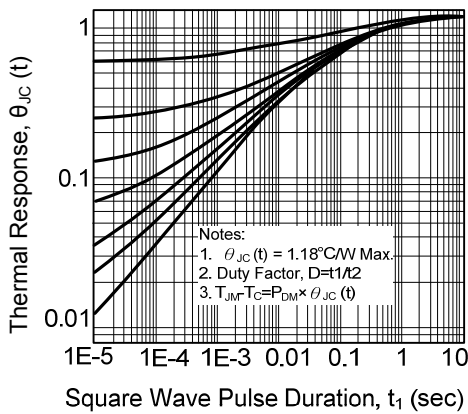
Capacitance Characteristics (Non-Repetitive)



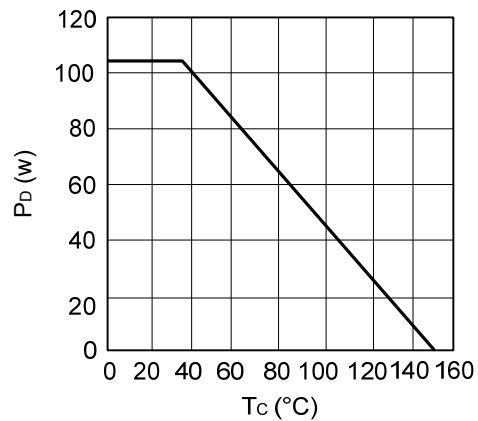
Gate Charge Characteristics



Transient Thermal Response Curve



Power Dissipation



UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.